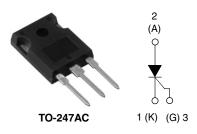


Vishay High Power Products

Phase Control SCR, 35 A



| PRODUCT SUMMARY | | | |
|------------------------|----------|--|--|
| V _T at 40 A | < 1.45 V | | |
| I _{TSM} | 500 A | | |
| V _{RRM} | 1600 V | | |

DESCRIPTION/FEATURES

The 40TPS16 High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature. Low Igt parts available.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level.

| MAJOR RATINGS AND CHARACTERISTICS | | | | | |
|------------------------------------|------------------------------|-------------|-------|--|--|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS | | |
| I _{T(AV)} | Sinusoidal waveform | 35 | А | | |
| I _{RMS} | | 55 | A | | |
| V _{RRM} /V _{DRM} | Range ⁽¹⁾ | 1600 | V | | |
| I _{TSM} | | 500 | А | | |
| V _T | 40 A, T _J = 25 °C | 1.45 | V | | |
| dV/dt | | 1000 | V/µs | | |
| dl/dt | | 100 | A/µs | | |
| TJ | | - 40 to 125 | °C | | |

Note

(1) Contact factory

| VOLTAGE RATINGS | | | | | |
|-----------------|---|---|---|--|--|
| PART NUMBER | V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V | I _{RRM} ∕I _{DRM} AT 125 °C mA | | |
| 40TPS16 | 1600 | 1700 | 10 | | |

Vishay High Power Products Phase Control SCR, 35 A



| ABSOLUTE MAXIMUM RATINGS | | | | | |
|--|------------------------------------|--|--|--------|------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum average on-state current | I _{T(AV)} | $T_C = 79 \ ^{\circ}C$, 180° conduction half sine w | ave | 35 | |
| Maximum continuous RMS on-state current as AC switch | I _{T(RMS)} | | | 55 | A |
| Maximum peak, one-cycle | 1 | 10 ms sine pulse, rated V_{RRM} applied | | 500 | |
| non-repetitive surge current | I _{TSM} | 10 ms sine pulse, no voltage reapplied | | 600 | |
| Movimum 12t for fusing | l ² t | 10 ms sine pulse, rated V_{RRM} applied | Initial T _J = T _J maximum | 1250 | A ² s |
| Maximum I ² t for fusing | 1-1 | 10 ms sine pulse, no voltage reapplied | | 1760 | A-S |
| Maximum I²√t for fusing | l²√t | t = 0.1 to 10 ms, no voltage reapplied | | 12 500 | A²√s |
| Low level value of threshold voltage | V _{T(TO)1} | - T _J = 125 °C | | 1.02 | V |
| High level value of threshold voltage | V _{T(TO)2} | | | 1.23 | v |
| Low level value of on-state slope resistance | r _{t1} | | | 9.74 | |
| High level value of on-state slope resistance | r _{t2} | | | 7.50 | mΩ |
| Maximum peak on-state voltage | V _{TM} | 110 A, T _J = 25 °C | | 1.85 | V |
| Maximum rate of rise of turned-on current | dl/dt | T _J = 25 °C | | 100 | A/μs |
| Maximum holding current | Ι _Η | | | 150 | |
| Maximum latching current | ١L | | | 300 | |
| | | $T_J = 25 ^{\circ}C$ | 1 | 0.5 | mA |
| Maximum reverse and direct leakage current | I _{RRM} /I _{DRM} | $V_{\rm R}$ = Rated $V_{\rm RRM}/V_{\rm DRM}$ | | 10 | |
| Maximum rate of rise of off-state voltage | dV/dt | $T_J = T_J$ maximum, linear to 80 % V _{DRM} , | R _g -k = Open | 1000 | V/µs |

| TRIGGERING | | | | | |
|---|--------------------|---|-----------------------------------|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum peak gate power | P _{GM} | | | 10 | W |
| Maximum average gate power | P _{G(AV)} | | | 2.5 | vv |
| Maximum peak gate current | I _{GM} | | | 2.5 | А |
| Maximum peak negative gate voltage | - V _{GM} | | | 10 | |
| Maximum required DC gate voltage to trigger | V _{GT} | T _J = - 40 °C | | 4.0 | v |
| | | T _J = 25 °C | Anode supply = 6 V resistive load | 2.5 | |
| | | T _J = 125 °C | | 1.7 | |
| | I _{GT} | T _J = - 40 °C | | 270 | |
| Maximum required DC acts surrent to trigger | | T _J = 25 °C | | 150 | |
| Maximum required DC gate current to trigger | | T _J = 125 °C | | 80 | mA |
| | | T _J = 25 °C, for 40 | TPS08A | 40 | |
| Maximum DC gate voltage not to trigger | V_{GD} | - T _J = 125 °C, V _{DRM} = Rated value | | 0.25 | V |
| Maximum DC gate current not to trigger | I _{GD} | | | 6 | mA |

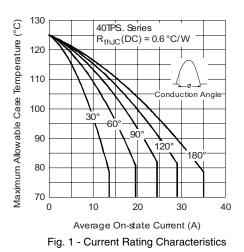


Phase Control SCR, 35 A Vishay High Power Products

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | | |
|---|--|-----------------------------------|--------------------------------------|-------------|------------|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Maximum junction and storage temperature range | | T _J , T _{Stg} | | - 40 to 125 | °C | |
| Maximum thermal resistance, junction to case | | R _{thJC} | DC operation | 0.6 | | |
| Maximum thermal resistance, junction to ambient | | R _{thJA} | | 40 | °C/W | |
| Maximum thermal resistance, case to heatsink | | R _{thCS} | Mounting surface, smooth and greased | 0.2 | | |
| | | | | 6 | g | |
| Approximate weight | | | | 0.21 | oz. | |
| Manualian tanana | minimum | | | 6 (5) | kgf ⋅ cm | |
| Mounting torque | maximum | | | 12 (10) | (lbf · in) | |
| Marking device | Marking device Case style TO-247AC 40TPS | | PS16 | | | |

Vishay High Power Products Phase Control SCR, 35 A





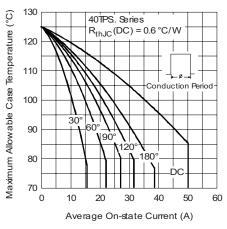


Fig. 2 - Current Rating Characteristics

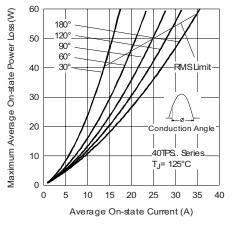


Fig. 3 - On-State Power Loss Characteristics

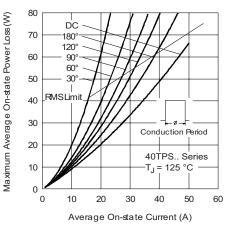


Fig. 4 - On-State Power Loss Characteristics

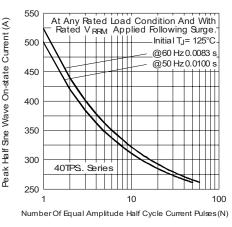


Fig. 5 - Maximum Non-Repetitive Surge Current

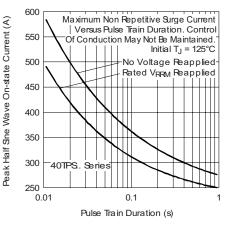


Fig. 6 - Maximum Non-Repetitive Surge Current



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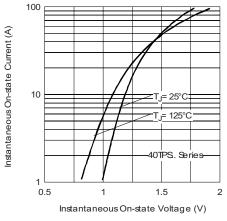


Fig. 7 - On-State Voltage Drop Characteristics

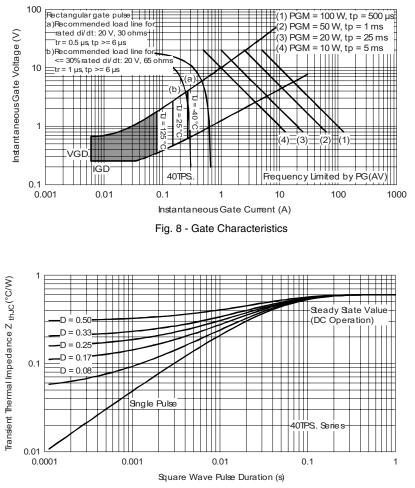
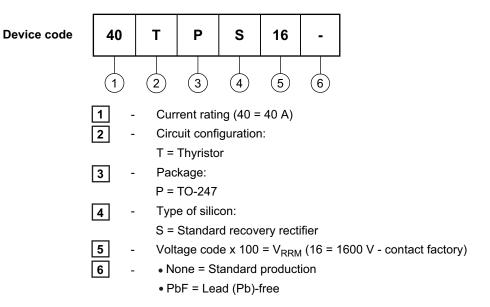


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

Vishay High Power Products Phase Control SCR, 35 A



ORDERING INFORMATION TABLE



| LINKS TO RELATED DOCUMENTS | | | |
|--|--|--|--|
| Dimensions http://www.vishay.com/doc?95024 | | | |
| Part marking information http://www.vishay.com/doc?95226 | | | |



Vishay

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